

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VHB40-28F is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB0}	65 V
V_{CE0}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.9 °C/W

PACKAGE STYLE .380 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10726

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 200 mA		35			V
BV_{CES}	I _C = 200 mA		65			V
BV_{CBO}	I _C = 10 mA		65			V
BV_{EBO}	I _E = 10 mA		4.0			V
I_{CB0}	V _{CB} = 30 V				1.0	mA
I_{CES}	V _{CE} = 30 V				10	mA
h_{FE}	V _{CE} = 5.0 V	I _C = 500 mA	5.0		200	---
C_{ob}	V _{CB} = 30 V	f = 1.0 MHz			65	pF
P_G	V _{CE} = 28 V	P _{IN} = 7.0 W	7.6			dB
η_C		f = 175 MHz	60			%